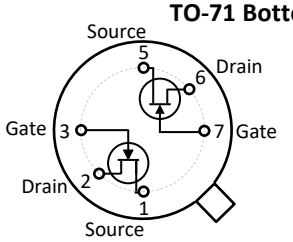
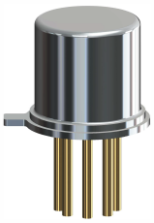
IFNU234, IFNU235 Dual Matched N-Channel JFET

Features

- InterFET N0016H Geometry
- Low Leakage: 10 pA Typical
- Low Input Capacitance: 3.5 pF Typical
- High Input Impedance
- Replacement for U234, U235
- RoHS Compliant
- SMT, TH, and Bare Die Package options.

TO-71 Bottom View

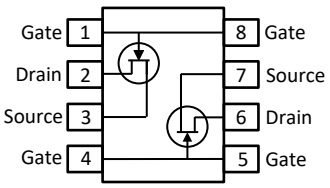




Applications

- Low Noise Differential Amplifier
- Differential Amplifier
- Wide-Band Amplifier

SOIC8 Top View



Description

The -50V InterFET IFNU234, and IFNU235 JFET's are targeted for low noise differential amplifier designs. Gate leakages are less than 10pA at room temperatures. The TO-71 package is hermetically sealed and suitable for military applications. Custom specifications, matching, and packaging options are available.

Product Summary

Parameters		IFNU234 Min	IFNU235 Min	Unit
BV_{GSS}	Gate to Source Breakdown Voltage	-50	-50	V
I_{DSS}	Drain to Source Saturation Current	0.5	0.5	mA
$V_{GS(off)}$	Gate to Source Cutoff Voltage	-0.5	-0.5	V
G_{FS}	Forward Transconductance	0.6	0.6	mS

Ordering Information Custom Part and Binning Options Available

Part Number	Description	Case	Packaging
IFNU234; IFNU235	Through-Hole	TO-71	Bulk
SMPU234; SMPU235	Surface Mount	SOIC8	Bulk
SMPU234TR; SMPU235TR	7" Tape and Reel: Max 500 Pieces 13" Tape and Reel: Max 2,500 Pieces	SOIC8	Minimum 500 Pieces Tape and Reel
IFNU234COT; IFNU235COT *	Chip Orientated Tray (COT Waffle Pack)	COT	70/Waffle Pack
IFNU234CFT; IFNU235CFT *	Chip Face-up Tray (CFT Waffle Pack)	CFT	70/Waffle Pack

* Bare die packaged options are designed for matched specifications but not 100% tested

Electrical Characteristics

Maximum Ratings (@ T_A = 25°C, Unless otherwise specified)

Parameters		Value	Unit
V_{RGS}	Reverse Gate Source and Gate Drain Voltage	-50	V
I_{FG}	Continuous Forward Gate Current	50	mA
P_D	Continuous Device Power Dissipation	300	mW
P	Power Derating	4.3	mW/°C
T_J	Operating Junction Temperature	-55 to 125	°C
T_{STG}	Storage Temperature	-65 to 150	°C

Static Characteristics (@ TA = 25°C, Unless otherwise specified)

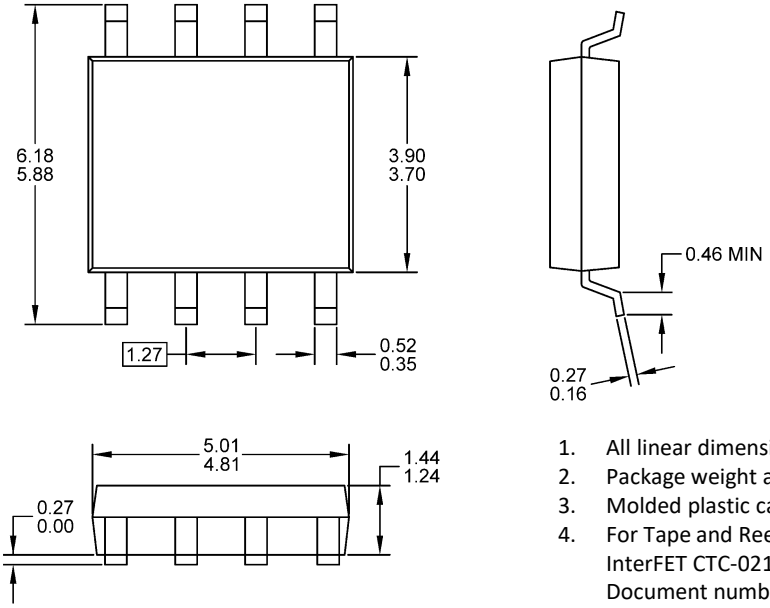
Parameters		Conditions	IFNU234, IFNU235		Unit
			Min	Max	
$V_{(BR)GSS}$	Gate to Source Breakdown Voltage	V_{DS} = 0V, I_G = -1µA	-50		V
I_{GSS}	Gate to Source Reverse Current	V_{GS} = -30V, V_{DS} = 0V, T_A = 25°C V_{GS} = -30V, V_{DS} = 0V, T_A = 150°C		-100 -500	pA nA
$V_{GS(OFF)}$	Gate to Source Cutoff Voltage	V_{DS} = 20V, I_D = 1nA	-0.5	-4.5	V
V_{GS}	Gate to Source Voltage	V_{DS} = 20V, I_D = 200µA	-0.3	-4	V
I_{DSS}	Drain to Source Saturation Current	V_{DS} = 20V, V_{GS} = 0V (Pulsed)	0.5		5
I_G	Gate Current	V_{DS} = 20V, I_D = 200µA, T_A = 25°C V_{DS} = 20V, I_D = 200µA, T_A = 125°C		-50 -250	pA nA

Dynamic Characteristics (@ TA = 25°C, Unless otherwise specified)

Parameters		Conditions		IFNU234, IFNU235		Unit
				Min	Max	
G_{FS}	Forward Transconductance	V_{DS} = 20V, I_D = 200µA, f = 1kHz		0.6	1.6	mS
G_{OS}	Output Conductance	V_{DS} = 20V, I_D = 200µA, f = 1kHz			10	µS
C_{iss}	Input Capacitance	V_{DS} = 20V, V_{GS} = 0V, f = 1MHz			6	pF
C_{rss}	Reverse Transfer Capacitance	V_{DS} = 20V, V_{GS} = 0V, f = 1MHz			2	pF
e_n	Equivalent Circuit Input Noise Voltage	V_{DS} = 20V, V_{GS} = 0V, f = 100Hz			80	nV/√Hz
$\lvert V_{GS1} - V_{GS2} \rvert$	Differential Gate Source Voltage	V_{DS} = 20V, I_D = 200µA	IFNU234 IFNU235	20 25		mV
$\frac{\lvert V_{GS1} - V_{GS2} \rvert}{\Delta T}$	Differential Gate Source Voltage with Temperature	V_{DS} = 20V, I_D = 200µA, T_A = -55°C, T_B = 25°C, T_C = 125°C	IFNU234 IFNU235	5 5		mV/°C

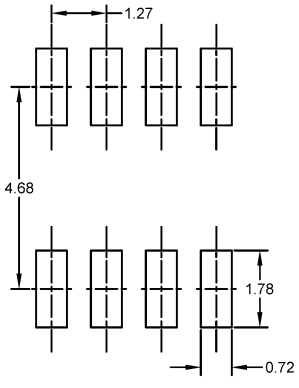
SOIC8 Mechanical and Layout Data

Package Outline Data



1. All linear dimensions are in millimeters.
2. Package weight approximately 0.21 grams
3. Molded plastic case UL 94V-0 rated
4. For Tape and Reel specifications refer to InterFET CTC-021 Tape and Reel Specification, Document number: IF39002
5. Bulk product is shipped in standard ESD shipping material
6. Refer to JEDEC standards for additional information.

Suggested Pad Layout



1. All linear dimensions are in millimeters.
2. The suggested land pattern dimensions have been provided for reference only. A more robust pattern may be desired for wave soldering.